Name of institution:

Institute for Experimental Physics
University of Hamburg
Address:
Luruper Chaussee 149
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Germany

Group members, devoted time:

Researcher:	
E. Fretwurst (contact person)	(50 %)
G. Lindström (retired)	(100 %)
I. Pintilie (guest phys.)	(80 %)
PhD's:	
J. Stahl	(100 %)
D. Contarato	(30 %)
Technical staff:	
P. Buhmann	(50 %)
U. Pein	(20 %)

Current related activities:

- Radiation damage basic studies (macroscopic parameters, annealing studies)
- Optimization of DOFZ material and investigation of other silicon material (SRD project in collaboration with Cis (Institute for Microsensoric, Erfurt/Germany))
- Defect characterization and defect kinetic studies
- Trapping studies
- Damage modeling and device simulation

Area of interest:

- Development of defect engineered silicon
- Defect characterization by C-DLTS, TSC and TCT and possible correlation with macroscopic parameters
- Device simulation of radiation damaged test-diodes and structured devices
- Trapping related effects
- Damage modeling
- Damage effects in thin micro structured devices

Available resources:

- Probe stations (C-V,I-V)
- C-DLTS (Laplace DLTS-optionally) and TSC, temperature range 15-400K
- Transient current technique (TCT), lasers : 675nm, 830nm, 1060nm
- Scanning laser test set up
- SEM
- ISE/TCAD device simulator